

PIMZ2; PUMZ2 NPN/PNP general-purpose double transistors Rev. 06 — 17 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/PNP general-purpose double transistors.

Table 1. **Product overview**

Type number	Package		Configuration
	NXP	JEITA	
PIMZ2	SOT457	SC-74	NPN/PNP double transistors
PUMZ2	SOT363	SC-88	NPN/PNP double transistors

1.2 Features

- Simplified circuit design
- Reduced component count
- Reduced pick and place costs

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current (DC)		-	-	150	mA

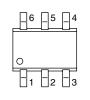


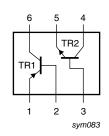
Pinning information

Table 3. **Pinning**

Pin	Description	Simplified outline	Symbol
PIMZ2 (S	OT457)		
1	collector TR2		
2	emitter TR2	<u> </u>	6 5 4
3	collector TR1	0	
4	emitter TR1	1 12 13	TR1
5	base TR1		TR2
6	base TR2		1 2 3
			sym082

PUMZ2 (SOT363) emitter TR1 2 base TR1 3 base TR2 4 collector TR2 5 emitter TR2 6 collector TR1





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3. Ordering information

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PIMZ2	SC-74	plastic surface mounted package; 6 leads	SOT457
PUMZ2	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking

Marking codes Table 5.

Type number	Marking code ^[1]
PIMZ2	M6
PUMZ2	GZ*

- [1] * = -: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

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Limiting values

Table 6. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pola	rity		
V_{CBO}	collector-base voltage	open emitter	-	60	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	7	V
I _C	collector current (DC)		-	150	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT457		[1] _	200	mW
	SOT363		[1] -	180	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device	9				
P _{tot}	total power dissipation	$T_{amb} \leq 25 ^{\circ}C$			
	SOT457		<u>[1]</u> -	300	mW
	SOT363		<u>[1]</u> _	300	mW

^[1] Device mounted on an FR4 printed-circuit board.

Thermal characteristics

Table 7. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT457		<u>[1]</u> _	-	625	K/W
	SOT363		<u>[1]</u> _	-	694	K/W
Per devid	ce					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT457		<u>[1]</u> _	-	417	K/W
	SOT363		<u>[1]</u> _	-	417	K/W

^[1] Device mounted on an FR4 printed-circuit board.

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7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Typ -	Max 100	Unit
-	100	
-	100	
	100	nA
-	50	μΑ
-	100	nA
250	560	
-	-500	mV
190	-	MHz
2.3	5	pF
-	250	mV
-	-	MHz
-	3	pF
	- 250 - 190 2.3	- 50 - 100 250 560 500 190 - 2.3 5 - 250

8. Package outline

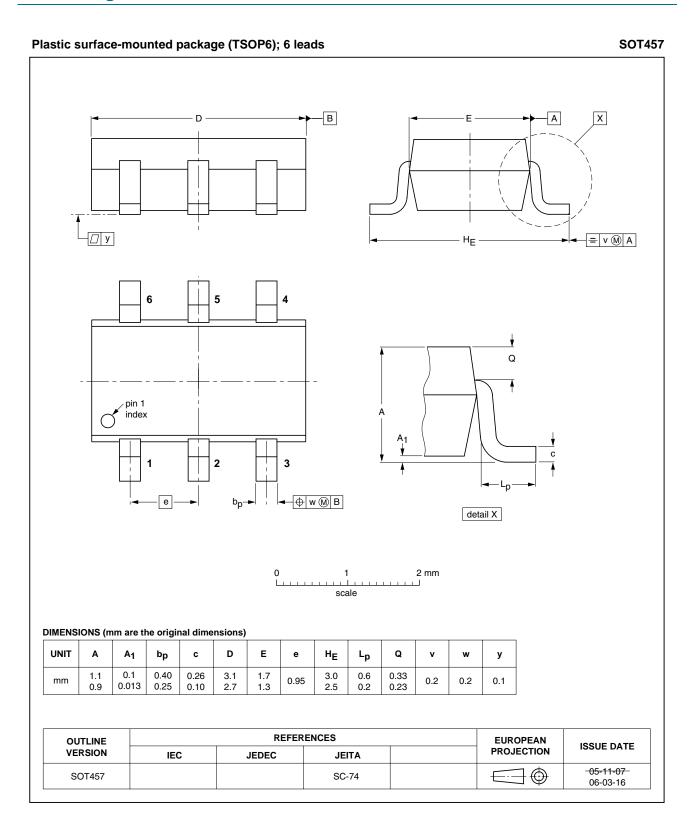
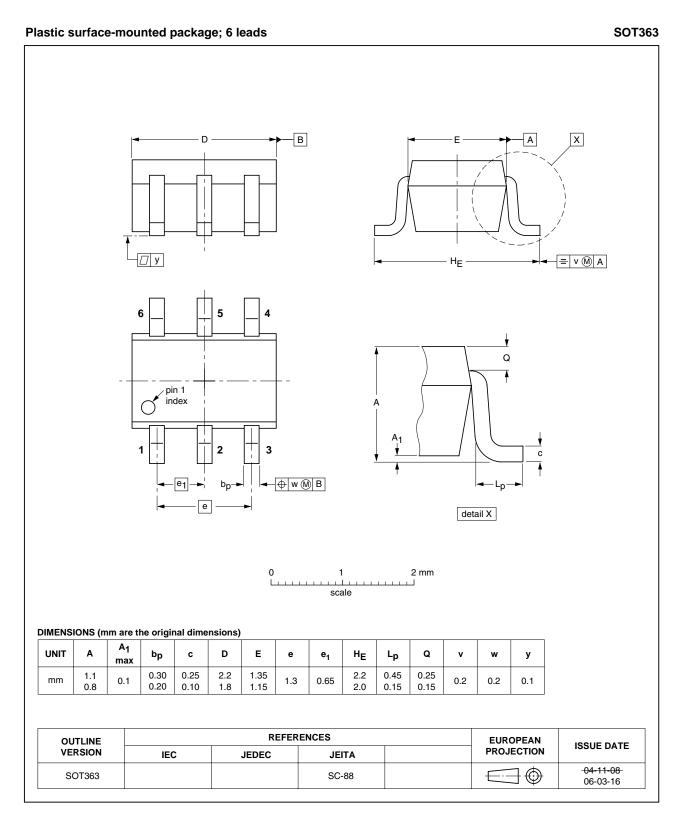


Fig 1. Package outline SOT457 (SC-74)

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Package outline SOT363 (SC-88)

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Revision history

Table 9. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PIMZ2_PUMZ2_6	20091117	Product data sheet	-	PIMZ2_PUMZ2_5
Modifications:	including net content. Table 3 "Pint Figure 1 "Pa	eet was changed to reflect to which legal definitions and disclanding": updated ckage outline SOT457 (SC-ckage outline SOT363 (SC-ckage outline SOT363 (SC-	aimers. No changes w	
PIMZ2_PUMZ2_5	20041124	Product data sheet	-	PIMZ2_PUMZ2_4
PIMZ2_PUMZ2_4	20031217	Product specification	-	PIMZ2_2
PIMZ2_2	20030714	Product specification	-	PIMZ2_1
PIMZ2_1	20030602	Objective specification	-	-

10. Legal information

Data sheet status 10.1

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com

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